

SG2500(FXF, GXH)21

GATE TURN-OFF THYRISTOR

TENTATIVE DATA

CHOPPER, INVERTER APPLICATION

- Repetitive Peak Off-State Voltage : $V_{DRM}=3300, 4500V$
- Repetitive Peak Reverse Voltage : $V_{DRM}=3000, 4000V$
- R.M.S On-State Current : $I_T(RMS)=800A$
- Peak Turn-Off Current : $I_{TGQM}=2500A$
- Critical Rate of Rise of On-State Current
: $di/dt=300A/\mu s$
- Critical Rate of Rise of Off-State Voltage
: $dv/dt=900V/\mu s$

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage	SG2500FXF21	V_{DRM}	3300	V
	SG2500GXH21		4500	
Repetitive Peak Reverse Voltage	SG2500FXF21	V_{RRM}	3000	V
	SG2500GXH21		4000	
Peak Turn-Off Current (Note 1)		I_{TGQM}	2500	A
R.M.S On-State Current (Note 2)		$I_T(RMS)$	800	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		I_{TSM}	14000(50Hz)	A
			15500(60Hz)	
Critical Rate of Rise of On-State Current (Note 3)		di/dt	300	A/ μs
Peak Forward Gate Current (Note 4)		I_{FGM}	45	A
Average Forward Gate Power Dissipation		$P_G(AV)$	14	W
R.M.S Reverse Gate Current		$I_{RG}(RMS)$	-	A
Peak Reverse Gate Power Dissipation (Note 5)		P_{RGM}	10	W
Peak Reverse Gate Voltage		V_{RGM}	15	V
Storage Temperature Range		T_{stg}	-40~115	°C
Operating Junction Temperature Range		T_j	-40~115	°C
Mounting Force		-	3300±200	kg

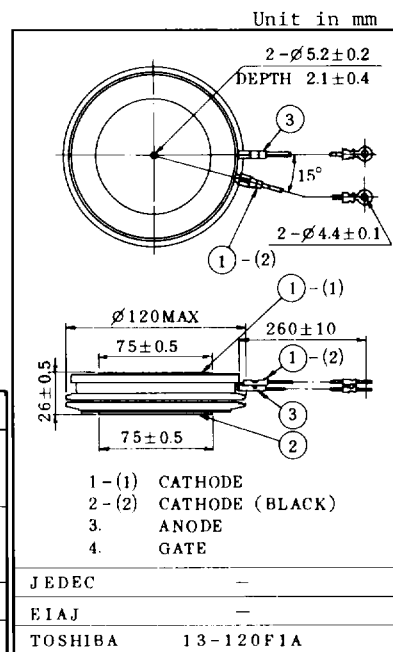
Note 1 : $V_D=1/2$ Rated, $C_S=6\mu F$, $R_S=5\Omega$, $di_{RG}/dt=-60A/\mu s$
 $I_{RG} \div 600A$, $T_j=115^\circ C$, ($V_{DSP} \leq 600V$)

Note 2 : Half sine waveform

Note 3 : $V_D=1/2$ Rated, $I_{TM}=2500A$, $I_G=20A$, $t_r=1\mu s$, $f=50Hz$, $T_j=115^\circ C$

Note 4 : Pulse width : Max. 20 μs , Duty : Max. 20%

Note 5 : Pulse width : Max. 20 μs , Duty : Max. 2%



ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Repetitive Peak Off-State Current	I_{DRM}	$V_{DRM} = \text{Rated}$, $R_{GK} = 5\Omega$ $T_j = 115^\circ\text{C}$	-	-	150	mA
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = \text{Rated}$, $T_j = 115^\circ\text{C}$	-	-	150	mA
Repetitive Peak Reverse Gate Current	I_{RGM}	$V_{RGM} = \text{Rated}$, $T_j = 115^\circ\text{C}$	-	-	100	mA
Peak On-State Voltage	V_{TM}	$I_{TM} = 2500\text{A}$, $T_c = 25^\circ\text{C}$	-	-	4.5	V
Gate Trigger Voltage	V_{GT}	$V_D = 24\text{V}$ $R_L = 0.2\Omega$	$T_c = -40^\circ\text{C}$	-	2.5	V
			$T_c = 25^\circ\text{C}$	-	1.5	
Gate Trigger Current	I_{GT}		$T_c = -40^\circ\text{C}$	-	4500	mA
			$T_c = 25^\circ\text{C}$	-	2500	
Gate Non-Trigger Voltage	V_{GD}	$V_D = 1/2 \text{ Rated}$, $T_c = 115^\circ\text{C}$	0.3	-	-	V
Gate Non-Trigger Current	I_{GD}		10	-	-	mA
Delay Time	t_d	$V_D = 1/2 \text{ Rated}$ $di/dt = 300\text{A}/\mu\text{s}$	-	-	8.0	μs
Turn-On Time	t_{gt}	$I_{TM} = 2500\text{A}$, $I_G = 20\text{A}$ $t_r = 1\mu\text{s}$, $T_c = 25^\circ\text{C}$	-	-	15.0	μs
Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{DRM} = 2/3 \text{ Rated}$ $T_j = 115^\circ\text{C}$, $V_{GK} = -4\text{V}$ Exponential Rise	900	-	-	$\text{V}/\mu\text{s}$
Holding Current	I_H	$T_c = 25^\circ\text{C}$, $R_L = 0.2\Omega$	-	-	80	A
Storage Time	t_s	$I_T = 2500\text{A}$, $V_D = 1/2 \text{ Rated}$	-	-	17	μs
Gate Turn-Off Time	t_{gq}	$V_{DM} = 2/3 \text{ Rated}$, $C_S = 6\mu\text{F}$	-	-	20	μs
Tail Time	t_{tail}	$di_{RG}/dt = -50\text{A}/\mu\text{s}$	-	-	180	μs
Turn-Off Gate Current	I_{RG}	$T_c = 110^\circ\text{C}$	-	550	600	A
Thermal Resistance	$R_{th(j-f)}$	Junction to Fin	-	-	0.02	$^\circ\text{C}/\text{W}$